Amendments to the Claims

1. (Currently Amended): A method of fabricating integrated circuitry comprising:

forming a conductive line having opposing sidewalls over a semiconductor substrate, the conductive line having an outer etch stop cap;

depositing an insulating layer over the substrate and the line;

planarize polishing the insulating layer using the outer etch stop cap as an etch stop;

after the planarize polishing, etching the insulating layer proximate the line along at least a portion of at least one sidewall of the line; and

after the etching, depositing an insulating spacer forming layer over the substrate and the line, and anisotropically etching it to form an insulating sidewall spacer along said portion of the at least one sidewall.

2. (Original): The method of claim 1 wherein the etching of the insulating layer is conducted along at least a portion of each of the opposing line sidewalls, the anisotropic etching forming an insulating sidewall spacer over each of the opposing line sidewalls.

3. (Original): The method of claim 1 wherein the etching of the insulating layer is conducted along the portion of the one sidewall and not along the opposing sidewall.

4. (Original): The method of claim 1 wherein the portion comprises a majority of said one sidewall.

5. (Original): The method of claim 1 wherein the portion comprises the substantial entirety of said at least one sidewall.

6. (Original): The method of claim 1 wherein the etching of the insulating layer outwardly exposes material of the semiconductor substrate.

7. (Original): The method of claim 1 wherein the conductive line is formed to comprise a transistor gate.

Claims 8-32 (Canceled).

33. (Currently Amended): A method of forming a conductive line comprising:

forming conductive material received over a semiconductor substrate into a line, the line having opposing sidewalls;

depositing insulative material over the line;

planarizing the insulative material;

depositing an insulating spacer forming layer over the line and the planarized insulative material; and

anisotropically etching the spacer forming layer to form a pair of insulative spacers over the opposing line sidewalls, the insulative material being received between at least one of the sidewalls and one insulative spacer formed thereover, the insulative material as received between the one sidewall and the one sidewall spacer formed thereover having a maximum lateral thickness which is greater than a maximum lateral thickness of the one sidewall spacer.

Claims 34-63 (Canceled).